

N-channel TrenchMOS logic level FET Rev. 2 — 7 February 2011

Product data sheet

#### 1. **Product profile**

#### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources

Motors, lamps and solenoids

Suitable for thermally demanding environments due to 175 °C rating

### 1.3 Applications

Table 1

- 12 V loads
- Automotive and general purpose power switching

Quick reference data

# 1.4 Quick reference data

Table 1.	QUICK reference	uata					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	[1]	-	-	75	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	300	W
Static cha	aracteristics						
R <sub>DSon</sub> drain-source on-state resistance	V <sub>GS</sub> = 4.3 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C		-	3.7	5.9	mΩ	
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C		-	2.9	4	mΩ
		$\label{eq:GS} \begin{array}{l} V_{GS} = 5 \; V; \; I_{D} = 25 \; A; \\ T_{j} = 25 \; ^{\circ}C; \; see \; \underline{Figure \; 11}; \\ see \; \underline{Figure \; 12} \end{array}$		-	3.5	4.4	mΩ



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Table 1.	Quick reference da	tacontinued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanch	e ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 75 \text{ A};  V_{sup} \leq 40 \text{ V}; \\ R_{GS} &= 50  \Omega;  V_{GS} = 5  V; \\ T_{j(\text{init})} &= 25 ^\circ\text{C};  \text{unclamped} \end{split}$	-	-	1.6	J
Dynamic	characteristics					
Q <sub>GD</sub>	gate-drain charge	$V_{GS} = 5 V; I_D = 25 A;$ $V_{DS} = 32 V; T_j = 25 °C;$ see Figure 13	-	56	-	nC

[1] Continuous current is limited by package.

### 2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain <sup>[1]</sup>	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2.

### 3. Ordering information

#### Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK9604-40A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

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# 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>DGR</sub>	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	40	V
V <sub>GS</sub>	gate-source voltage			-15	15	V
I <sub>D</sub>	drain current	$T_{mb}$ = 100 °C; $V_{GS}$ = 5 V; see <u>Figure 1</u>	<u>[1]</u>	-	75	А
		$T_{mb} = 25 \text{ °C}; V_{GS} = 5 \text{ V}; \text{ see } Figure 1;$	<u>[1]</u>	-	75	А
		see Figure 3		-	198	А
I <sub>DM</sub>	peak drain current	T <sub>mb</sub> = 25 °C; pulsed; t <sub>p</sub> ≤ 10 μs; see <u>Figure 3</u>		-	794	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	300	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
Is	source current	T <sub>mb</sub> = 25 °C	[3]	-	198	А
		[1]		-	75	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	794	А
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 75 A; $V_{sup} \le 40$ V; $R_{GS} = 50$ Ω; $V_{GS} = 5$ V; $T_{j(init)} = 25$ °C; unclamped		-	1.6	J

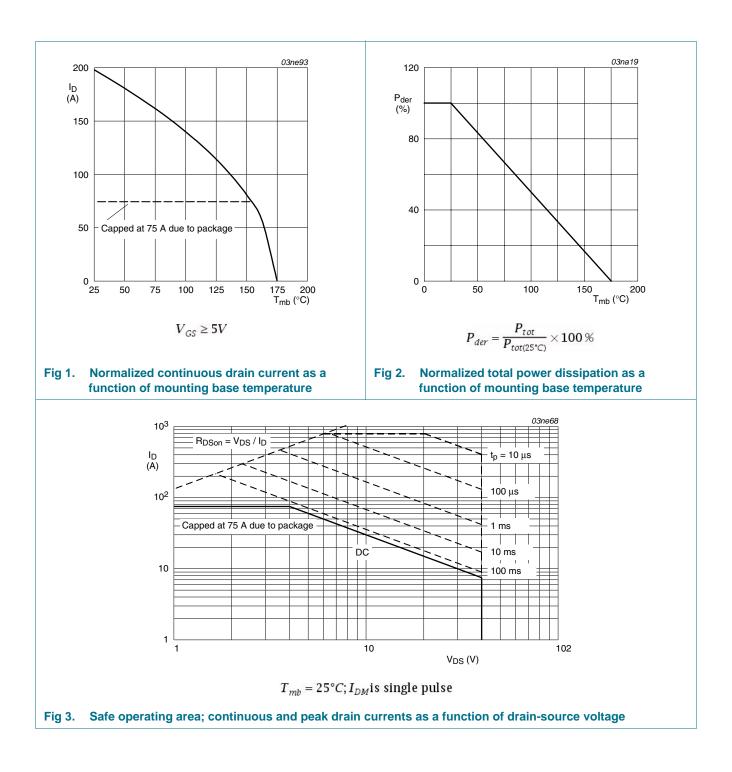
[1] Continuous current is limited by package.

[2] Current is limited by power dissipation chip rating.

[3] Current is limited by power dissipation chip rating

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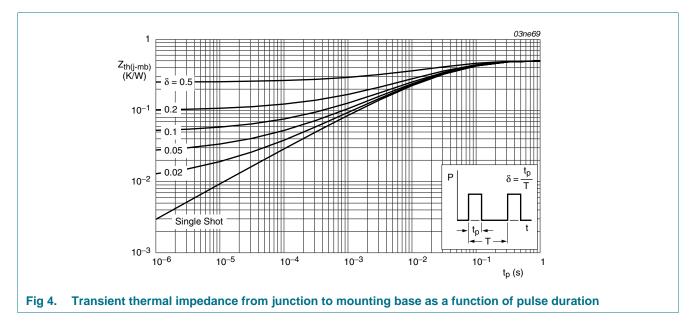
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#### **Thermal characteristics** 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see Figure 4	-	-	0.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	mounted on printed circuit board; minimum footprint	-	50	-	K/W



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# 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	40	-	-	V
	breakdown voltage	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	36	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; see <u>Figure 10</u>	1	1.5	2	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; see <u>Figure 10</u>	0.5	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; see <u>Figure 10</u>	-	-	2.3	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 10 \text{ V};  V_{DS} = 0 \text{ V};  T_j = 25 ^{\circ}\text{C}$	-	2	100	nA
		$V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 4.3 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	3.7	5.9	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	2.9	4	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	8.3	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	3.5	4.4	mΩ
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 5 \text{ V};$	-	128	-	nC
Q <sub>GS</sub>	gate-source charge	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{13}$	-	13	-	nC
Q <sub>GD</sub>	gate-drain charge		-	56	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	6200	8260	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 14</u>	-	1040	1250	pF
C <sub>rss</sub>	reverse transfer capacitance		-	680	940	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; $R_L$ = 1.2 $\Omega$ ; $V_{GS}$ = 5 V;	-	62	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	309	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	365	-	ns
t <sub>f</sub>	fall time		-	306	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ °C}$	-	2.5	-	nH
		from drain lead 6 mm from package to centre of die; $T_j = 25 \text{ °C}$	-	4.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bond pad; $T_j = 25 \text{ °C}$	-	7.5	-	nH

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ble 6.	Characteristics continued	Conditions			<b>T</b>	M	11!!
/mbol	Parameter	Conditions		Min	Тур	Max	Unit
	rain diode				0.05	4.0	N
SD	source-drain voltage	$I_S = 40 \text{ A}; V_{GS} = 0 \text{ V}$ see <u>Figure 15</u>	·	-	0.85	1.2	V
	reverse recovery time	$I_{\rm S} = 20 \text{ A}; \text{ d}I_{\rm S}/\text{d}t = -1$		-	260	-	ns
	recovered charge	V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 3	$30 \text{ V}; \text{ I}_{\text{j}} = 25 \text{ °C}$	-	531	-	nC
				9 $f_j = 25^{\circ}C; I_D =$ the on-state re	= 25A	03nd94	Inction
	function of drain-source volt			rce voltage;			
10 <sup>-3</sup>	min <u>/</u> / / / / / / / / / / / / / /		60 40				
10 <sup>-5</sup>		3		40	60	80 I <sub>D</sub> (A)	
10 <sup>-6</sup>	0 1 2	V <sub>GS</sub> (V)				.0 (, ,)	
	0 1 2 $T_j = 25 ^{\circ}C; V_{DS} = V_0$	V <sub>GS</sub> (V)	$T_{j}$	$= 25^{\circ}C; V_{DS}$			

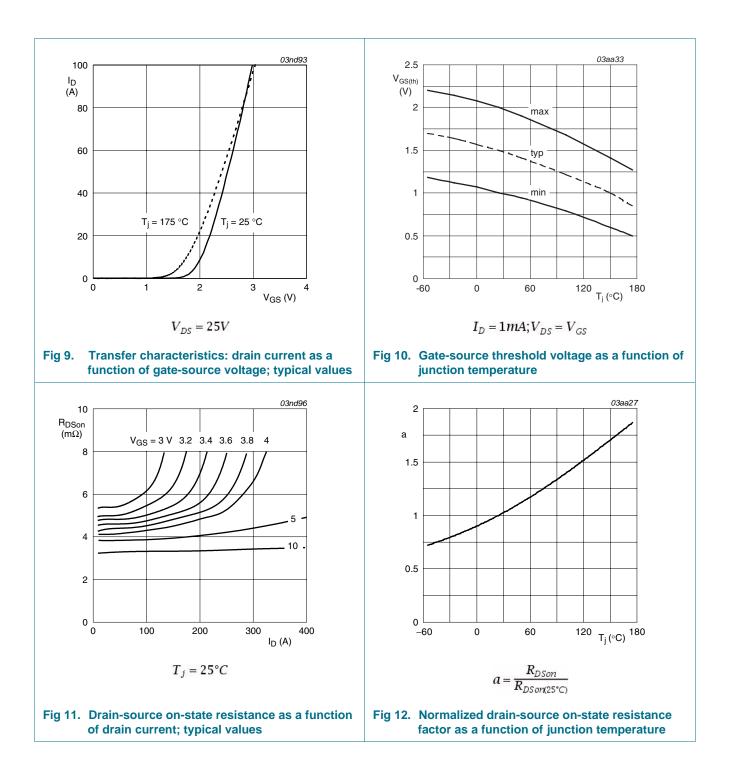
#### Table 6. Characteristics ...continued

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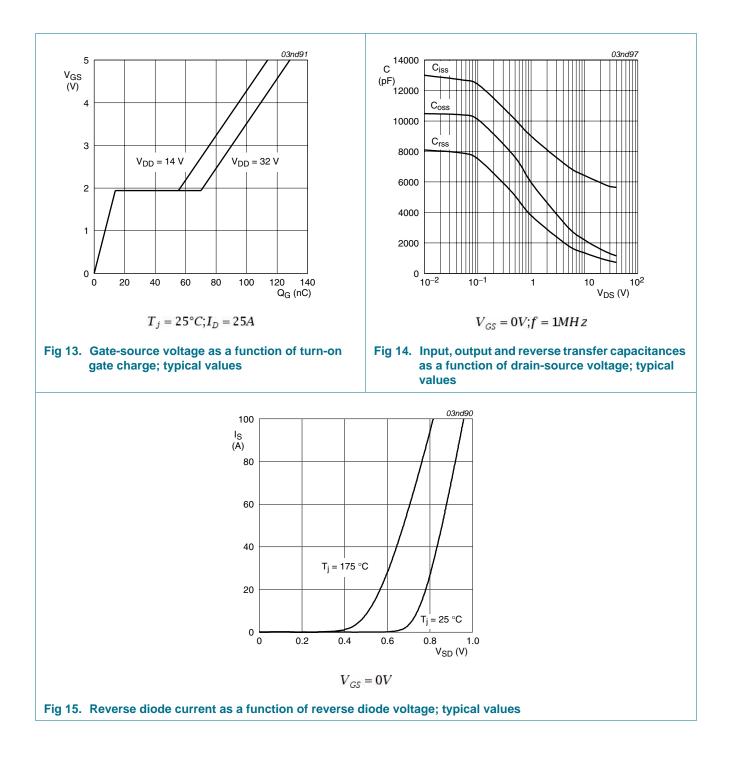
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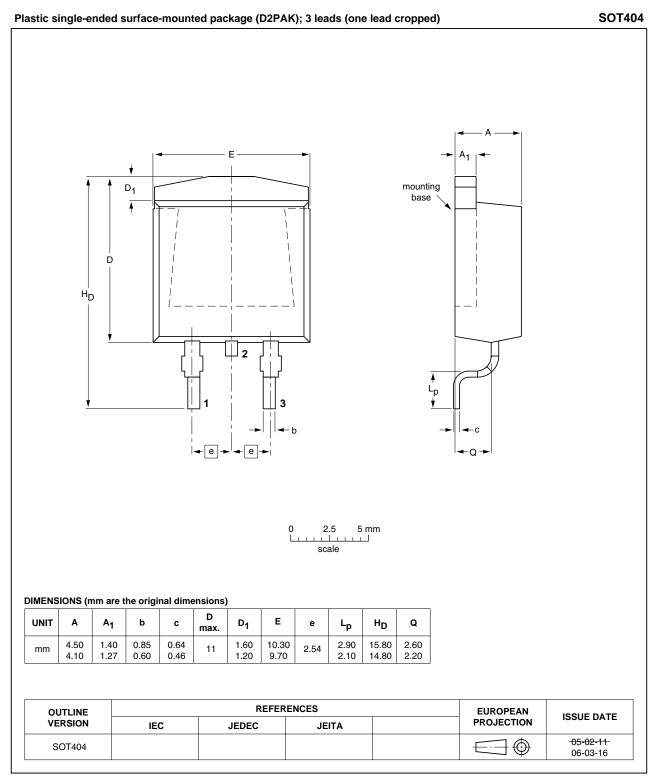
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### 7. Package outline



#### Fig 16. Package outline SOT404 (D2PAK)

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# 8. Revision history

Table 7.	<b>Revision history</b>					
Document	ID	Release date	Data sheet status	Change notice	Supersedes	
BUK9504-4	40A v.2	20110207	Product data sheet	-	BUK95_96_9E04_40A-01	
Modifications:		<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> </ul>				
		<ul> <li>Legal texts</li> </ul>	have been adapted to the	new company nam	e where appropriate.	
		<ul> <li>Type number</li> </ul>	er BUK9504-40A separate	d from data sheet E	3UK95_96_9E04_40A-01.	
BUK95_96	_9E04_40A-01	20011024	Product specification	-	-	

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### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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